

## Features

- Trench Power LV MOSFET Technology
- Excellent Package for Heat Dissipation
- + High Density Cell Design for Low  $R_{\text{DS}(\text{ON})}$
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

### **Maximum Ratings**

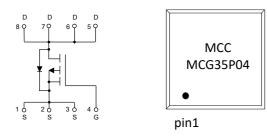
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 3.3°C/W Junction to Case<sup>(2)</sup>
- Thermal Resistance: 150°C/W Junction to Ambient<sup>(2)</sup>

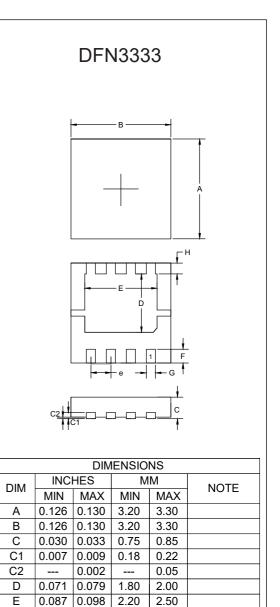
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	-40	V
Gate-Source Volltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	-35	Α
Pulsed Drain Current <sup>(3)</sup>	I <sub>DM</sub>	-140	Α
Total Power Dissipation	P <sub>D</sub>	38	W
Single Pulsed Avalanche Energy <sup>(4)</sup>	E <sub>AS</sub>	50	mJ

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The Value of R<sub>6JA</sub> is Measured with the Device Mounted on 1in2 FR-4 Board with 2oz. Copper, in a Still Air Environment with T<sub>A</sub>=25°C. The Value in Any Given Application Depends on the User's Specific Board Design.
  - the Value of  $R_{\text{BJC}}$  is Measured with Surface Mounted on 1 in^2  $\mbox{ pad area, } t{\leq}10$  sec.
- 3. Pulse Test: Pulse Width  $\leq$  300us, Duty cycle  $\leq$  2%.
- 4. V<sub>DS</sub>=-35V, V<sub>GS</sub>=-10V, L=1mH.
- 5. For design aid only, not subject to production testing.

### Internal Structure and Marking Code





0.50

0.35

0.40

0.70

0.40

0.25

0.30

0.60

**P-CHANNEL** 

MOSFET

F

G

н

е

0.016 0.020

0.010 0.014

0.012 0.016

0.024 0.028

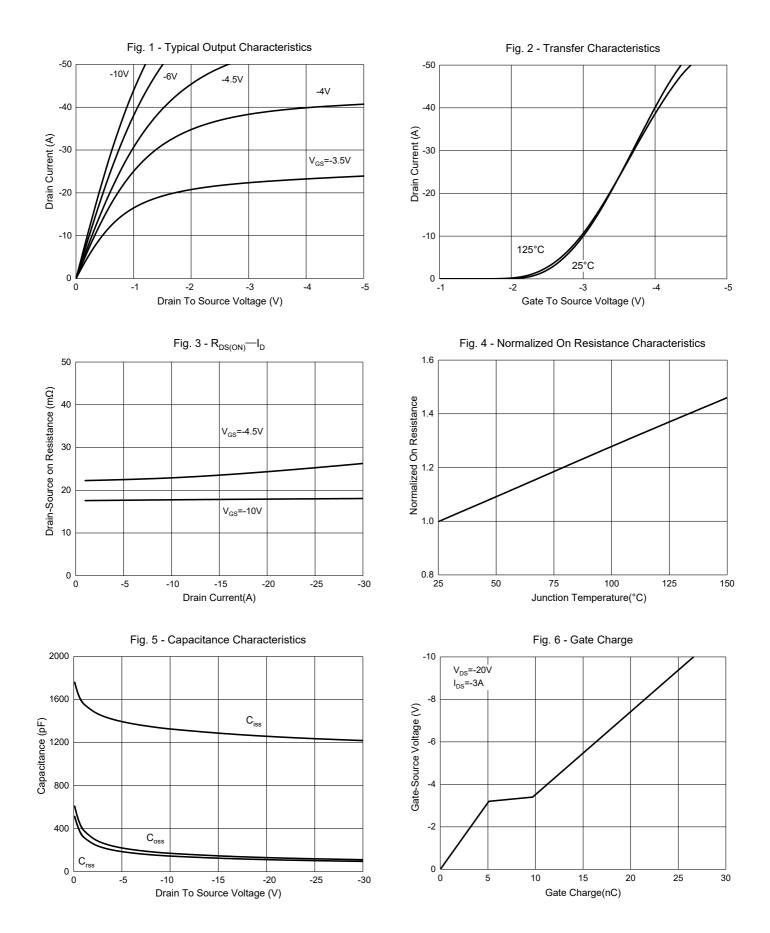


## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics			L	1	1	1	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250µA	-40			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V			-1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250µA	-1	-1.7	-2.5	V	
	D	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A		17	25	mΩ	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A		25	35	mΩ	
Forward Transconductance (3)(5)	gfs	V <sub>DS</sub> =-5V, I <sub>D</sub> =-1A		5.5		S	
Diode Characteristics							
Continuous Body Diode Current	Is				-35	A	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-20A			-1.3	V	
Reverse Recovery Time	t <sub>rr</sub>			21.5		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	l <sub>F</sub> =-12A, dl <sub>F</sub> /dt=100A/µs		5		nC	
Dynamic Characteristics				1	1		
Input Capacitance	C <sub>iss</sub>			1257			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V,f=1MHz		129		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			110		1	
Total Gate Charge	Qg			26.6			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-3A		5.1		nC	
Gate-Drain Charge	Q <sub>gd</sub>			4.6		•	
Turn-On Delay Time	t <sub>d(on)</sub>			5.4			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-10V,		21.5			
Turn-Off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> =3.3Ω, I <sub>DS</sub> =-3A		94.7		- ns	
Turn-Off Fall Time	t <sub>f</sub>			45.2			



# **Curve Characteristics**





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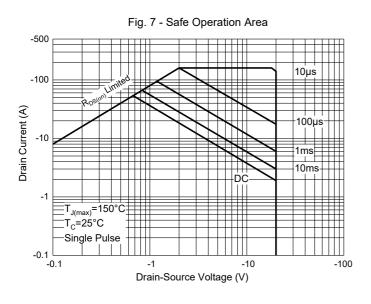
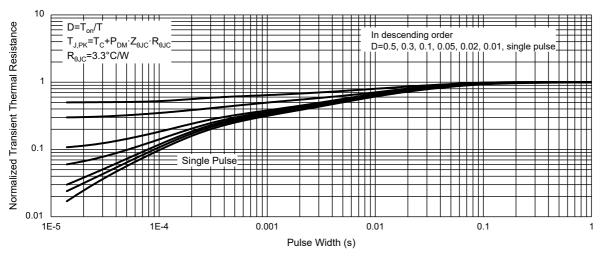


Fig. 8 - Normalized Maximum Transient Thermal Impedance







# **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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